**Product data sheet** 

## 1. General description

Planar passivated four quadrant triac in a SOT223 surface-mountable plastic package intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance.

### 2. Features and benefits

- High blocking voltage capability
- · Planar passivated for voltage ruggedness and reliability
- Surface-mountable package
- · Triggering in all four quadrants
- · Very sensitive gate

## 3. Applications

- · General purpose low power motor control
- · General purpose switching and phase control

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DRM}$	repetitive peak off- state voltage		-	-	600	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{sp} \le 110 \text{ °C}$ ; $\overline{Fig. 1}$ ; $\overline{Fig. 2}$ ; $\overline{Fig. 3}$	-	-	1	А
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; Fig. 4; Fig. 5	-	-	12.5	А
		full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 16.7 \text{ ms}$	-	-	13.8	А
Tj	junction temperature		-	-	125	°C
Static charac	teristics					
I <sub>GT</sub>	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	0.4	3	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 9$	-	1.3	3	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	1.4	3	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 9}}{}$	-	3.8	7	mA

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>		-	1.3	5	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 1.4 A; T <sub>j</sub> = 25 °C; <u>Fig. 12</u>		-	1.2	1.5	V
Dynamic chara	Dynamic characteristics						
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; $R_{GT1(ext)}$ = 1 k $\Omega$ ; Fig. 14		10	20	-	V/µs
dV <sub>com</sub> /dt	rate of change of commutating voltage	$V_D$ = 400 V; $T_j$ = 125 °C; $dI_{com}/dt$ = 0.5 A/ms; $I_T$ = 1 A; gate open circuit		2	-	-	V/µs

# 5. Pinning information

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	4	T2—T1
2	T2	main terminal 2		G sym051
3	G	gate		Symost
4	T2	mainterminal 2	⊟1 ⊟2 ⊟3 SC-73 (SOT223)	

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package		
	Name	Description	Version
BT131W-600	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223

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## 7. Limiting values

### **Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	600	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{sp} \le 110 ^{\circ}\text{C}$ ; $\overline{\text{Fig. 1}}$ ; $\overline{\text{Fig. 2}}$ ; $\overline{\text{Fig. 3}}$	-	1	Α
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 20 ms; Fig. 4; Fig. 5	-	12.5	Α
		full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 16.7 \text{ ms}$	-	13.8	Α
I <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; SIN	-	0.78	A²s
dl <sub>T</sub> /dt	rate of rise of on-state current	I <sub>G</sub> = 6 mA	-	50	A/µs
			-	50	A/µs
		I <sub>G</sub> = 14 mA	-	10	A/µs
		I <sub>G</sub> = 6 mA	-	50	A/µs
I <sub>GM</sub>	peak gate current		-	2	Α
$P_{GM}$	peak gate power		-	5	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.5	W
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

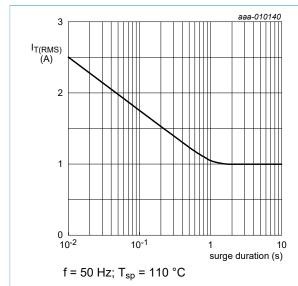


Fig. 1. RMS on-state current as a function of surge duration; maximum values

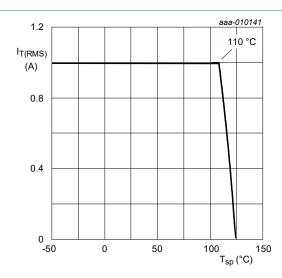


Fig. 2. RMS on-state current as a function of solder point temperature; maximum values

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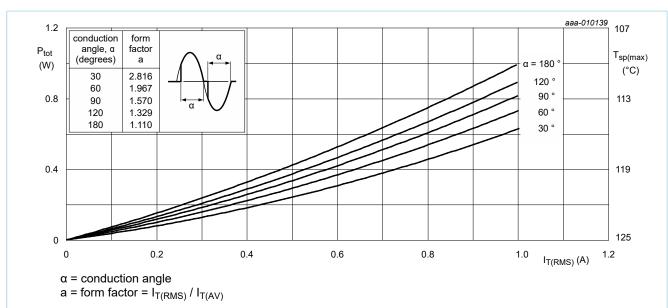


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

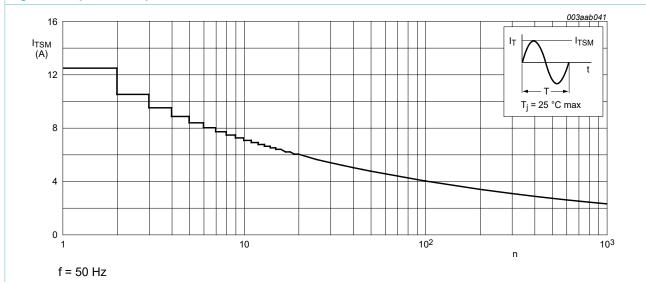
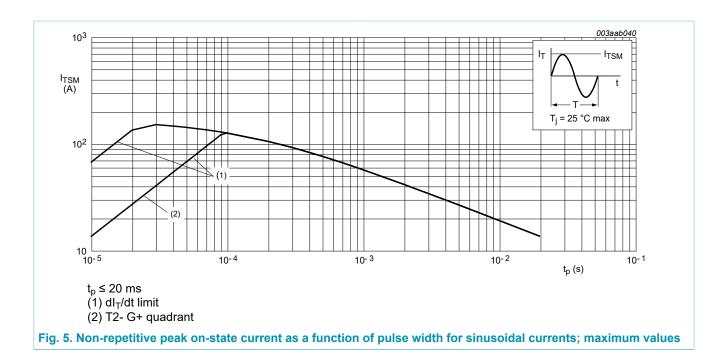


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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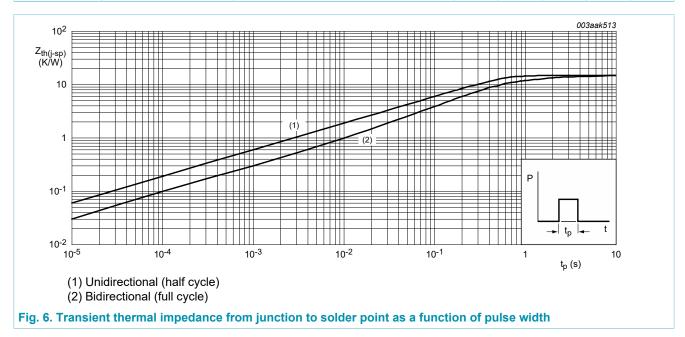
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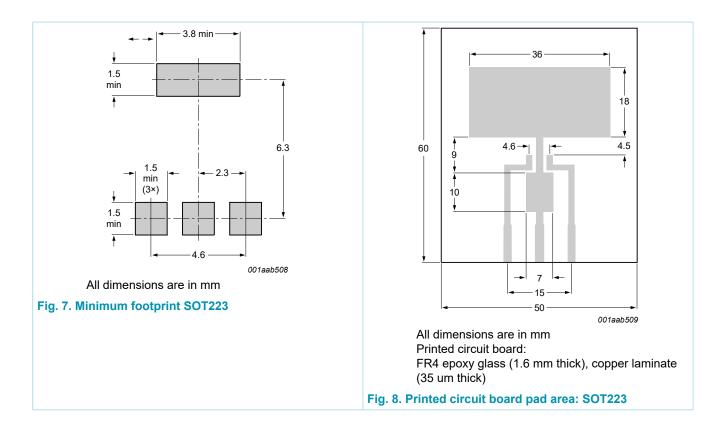
### 8. Thermal characteristics

**Table 5. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point	full cycle; Fig. 6	-	-	15	K/W
$R_{th(j-a)}$	thermal resistance from junction to	in free air; printed circuit board mounted; minimum footprint; Fig. 7	-	156	-	K/W
	ambient free air	in free air; printed circuit board mounted; pad area; Fig. 8	-	70	-	K/W



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### 9. Characteristics

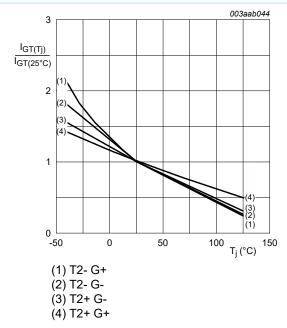
#### **Table 6. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; } Fig. 9$	-	0.4	3	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 9$	-	1.3	3	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2-\text{ G-;} $ $T_j = 25 ^{\circ}\text{C; } \underline{\text{Fig. 9}}$	-	1.4	3	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2-\text{ G+;}$ $T_j = 25 \text{ °C; } \underline{Fig. 9}$	-	3.8	7	mA
L	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 10$	-	1.2	5	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 10$	-	4	8	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2- \text{ G-};$ $T_j = 25 ^{\circ}\text{C}; \frac{\text{Fig. } 10}{\text{ C}}$	-	1	5	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2- G+;$ $T_j = 25 \text{ °C}; Fig. 10$	-	2.5	8	mA
l <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	1.3	5	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 1.4 A; T <sub>j</sub> = 25 °C; <u>Fig. 12</u>	-	1.2	1.5	V
$V_{GT}$	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 13	-	0.7	1	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ Fig. 13	0.2	0.3	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 600 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamic ch	naracteristics		·			
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; $T_j$ = 125 °C; $(V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; $R_{GT1(ext)}$ = 1 k $\Omega$ ; Fig. 14	10	20	-	V/µs
dV <sub>com</sub> /dt	rate of change of commutating voltage	$V_D$ = 400 V; $T_j$ = 125 °C; $dI_{com}/$ dt = 0.5 A/ms; $I_T$ = 1 A; gate open circuit	2	-	-	V/µs
t <sub>gt</sub>	gate-controlled turn-on time	$I_{TM}$ = 1.5 A; $V_D$ = 600 V; $I_G$ = 0.1 A; $dI_G/dt$ = 5 A/ $\mu$ s	-	2	-	μs

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 $I_{\mathsf{L}}$ I<sub>L(25°C)</sub> 2 1 0 -50 0 50 100 <sub>Tj</sub> (°C) 150

Fig. 10. Normalized latching current as a function of junction temperature

Fig. 9. Normalized gate trigger current as a function of junction temperature

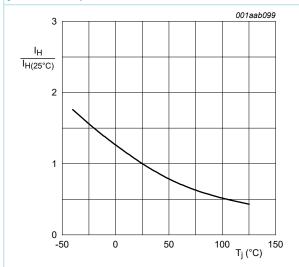
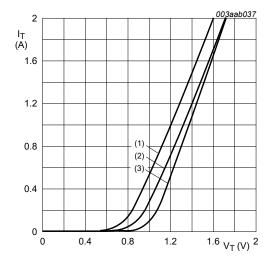


Fig. 11. Normalized holding current as a function of junction temperature

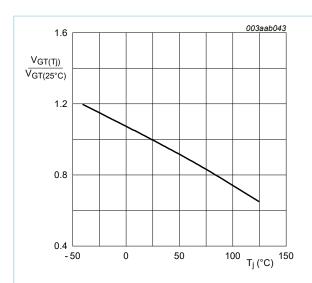


 $V_o$  = 0.92 V;  $R_s$  = 0.4 Ω (1)  $T_j$  = 125 °C; typical values (2)  $T_j$  = 125 °C; maximum values

(3) T<sub>i</sub> = 25 °C; maximum values

Fig. 12. On-state current as a function of on-state voltage

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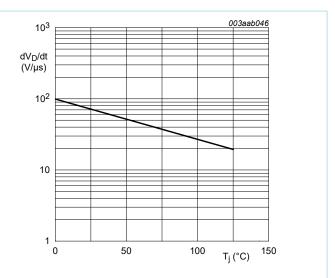


Fig. 14. Rate of rise of off-state voltage as a function of junction temperature; typical values

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## 10. Package outline

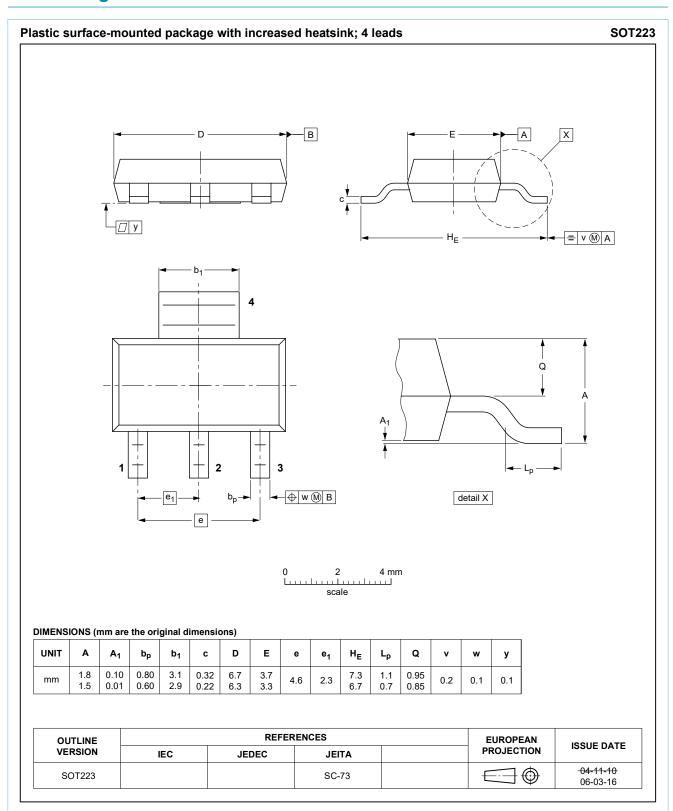
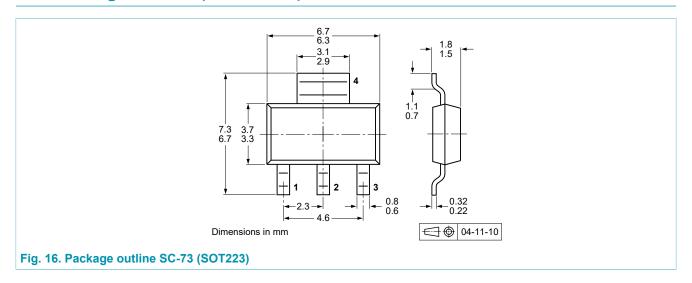


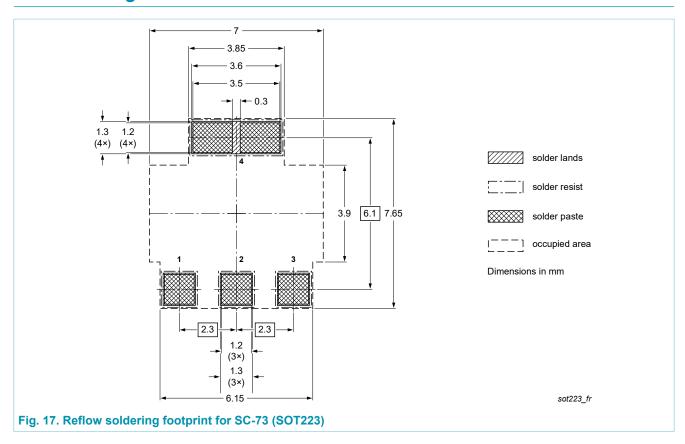
Fig. 15. Package outline SC-73 (SOT223)

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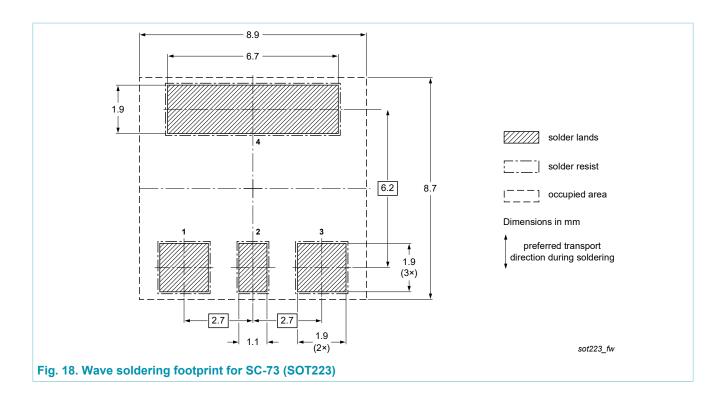
## 11. Package outline (minimized)



## 12. Soldering



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## 13. Legal information

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Document status [1][2]	Product status [3]	Definition
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